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- **Member of the Texas Instruments** Widebus™ Family
- **EPIC** ™ (Enhanced-Performance Implanted **CMOS) Submicron Process**
- B-Port Outputs Have Equivalent 26- Ω Series Resistors, So No External Resistors **Are Required**
- **ESD Protection Exceeds 2000 V Per** MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per **JESD 17**
- Bus Hold on Data Inputs Eliminates the **Need for External Pullup/Pulldown** Resistors
- **Package Options Include Thin-Shrink** Small-Outline (DGG) and Plastic Shrink Small-Outline (DL) Packages

NOTE: For tape and reel order entry: The DGGR package is abbreviated to GR.

description

This 12-bit to 24-bit multiplexed D-type latch is designed for 1.65-V to 3.6-V_{CC} operation.

The SN74ALVCH162260 is used in applications in which two separate data paths must be multiplexed onto, or demultiplexed from, a single applications data path. Typical include multiplexing and/or demultiplexing address and information in microprocessor bus-interface applications. This device also is useful in memory-interleaving applications.

DGG OR DL PACKAGE (TOP VIEW)

OEA	Н	4	\cup	EC	OE2B
_	コ	1		56	Р -
LE1B	_	2			LEA2B
2B3	_			54	E .
GND	ᇽ	4		53	GND
2B2	Ц	5		52	2B5
2B1	Q	6		51] 2B6
V_{CC}	Q	7		50] v _{cc}
A1	Q	8		49] 2B7
A2	q	9		48] 2B8
АЗ	٥	10		47] 2B9
GND	q	11		46] GND
A4	9	12		45	2B10
A5	Q	13		44	2B11
A6	Q	14		43	2B12
A7	٩	15		42] 1B12
A8				41] 1B11
A9	Q	17		40] 1B10
GND	q	18		39] GND
A10	O	19		38] 1B9
A11	D	20		37] 1B8
A12	٥	21		36] 1B7
V_{CC}	٥	22		35]v _{cc}
	q	23		34] 1B6
1B2	q	24		33] 1B5
GND	٥	25		32	GND
1B3	d	26		31] 1B4
LE2B	d	27		30	LEA1B
SEL	þ	28		29	OE1B

Three 12-bit I/O ports (A1-A12, 1B1-1B12, and 2B1-2B12) are available for address and/or data transfer. The output-enable (OE1B, OE2B, and OEA) inputs control the bus transceiver functions. The OE1B and OE2B control signals also allow bank control in the A-to-B direction.

Address and/or data information can be stored using the internal storage latches. The latch-enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch-enable input is high, the latch is transparent. When the latch-enable input goes low, the data present at the inputs is latched and remains latched until the latch-enable input is returned high.

The B outputs, which are designed to sink up to 12 mA, include equivalent 26- Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.



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description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162260 is characterized for operation from -40° C to 85° C.

Function Tables

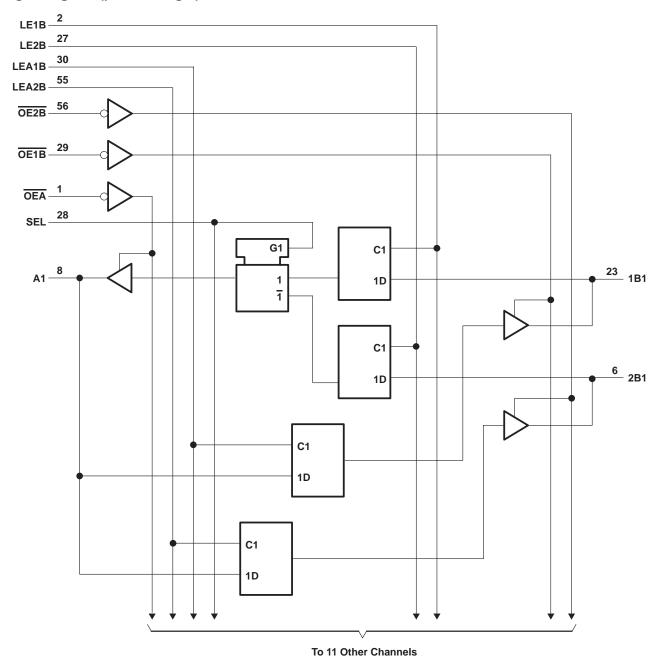
B TO A (OEB = H)

	INPUTS						
1B	2B	SEL	LE1B	LE2B	OEA	Α	
Н	Χ	Н	Н	Х	L	Н	
L	Χ	Н	Н	X	L	L	
Х	Χ	Н	L	Χ	L	A ₀	
Х	Н	L	X	Н	L	Н	
Х	L	L	X	Н	L	L	
Х	Χ	L	Χ	L	L	A ₀	
Х	Χ	Χ	X	X	Н	Z	

A TO B
(OEA = H)

(0=11=11)								
		OUTI	PUTS					
Α	LEA1B	LEA2B	OE1B	OE2B	1B	2B		
Н	Н	Н	L	L	Н	Н		
L	Н	Н	L	L	L	L		
Н	Н	L	L	L	Н	2B ₀		
L	Н	L	L	L	L	2B ₀		
Н	L	Н	L	L	1B ₀	Н		
L	L	Н	L	L	1B ₀	L		
Х	L	L	L	L	1B ₀	2B ₀		
Х	X	Χ	Н	Н	Z	Z		
Х	Χ	Χ	L	Н	Active	Z		
Х	Χ	Χ	Н	L	Z	Active		
Х	X	Χ	L	L	Active	Active		

logic diagram (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	Note 1) and 2) DGG package DGV package	-0.5 V to 4.6 V -0.5 V to V _{CC} + 0.5 V -0.5 V to V _{CC} + 0.5 V -50 mA -50 mA ±50 mA ±100 mA 81°C/W 86°C/W
Storage temperature range, T _{stg}	DL package	74°C/W

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. This value is limited to 4.6 V maximum.
- 3. The package thermal impedance is calculated in accordance with JESD 51.



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recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
VCC	Supply voltage		1.65	3.6	V	
VIH		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}			
	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2			
.,		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		
V_{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
	V _{CC} = 2.7 V			0.8		
٧ _I	Input voltage		0	VCC	V	
٧o	Output voltage		0	Vcc	V	
		V _{CC} = 1.65 V		-4		
	Lligh level cutout current (A part)	V _{CC} = 2.3 V		-12		
	High-level output current (A port)	V _{CC} = 2.7 V		-12		
la		V _{CC} = 3 V		-24	A	
ЮН		V _{CC} = 1.65 V		-2	mA	
	High-level output current (B port)	V _{CC} = 2.3 V		-6		
	High-level output current (B port)	V _{CC} = 2.7 V		-8	1	
		V _{CC} = 3 V		-12		
		V _{CC} = 1.65 V		4		
	Low-level output current (A port)	V _{CC} = 2.3 V		12		
	Low-level output current (A port)	V _{CC} = 2.7 V	12			
la.		V _{CC} = 3 V		24	mA	
IOL		V _{CC} = 1.65 V		2	IIIA	
	Low lovel output ourrent (D port)	V _{CC} = 2.3 V		6	7	
	Low-level output current (B port)	V _{CC} = 2.7 V		8		
	V _{CC} = 3 V			12		
Δt/Δν	Input transition rise or fall rate	-		10	ns/V	
T _A	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

VOH	A port	$I_{OH} = -100 \mu A$ $I_{OH} = -4 mA$ $I_{OH} = -6 mA$	1.65 V to 3.6 V 1.65 V	V _{CC} -0.2			
	A port		1.65 V	1.2			
	A port		i	1.2			
	A port		2.3 V	2			
VOH			2.3 V	1.7		1 !	
VOH -		$I_{OH} = -12 \text{ mA}$	2.7 V	2.2			
VOH			3 V	2.4			
voн Г		I _{OH} = -24 mA	3 V	2			
		I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.2		V	
		I _{OH} = -2 mA	1.65 V	1.2			
		$I_{OH} = -4 \text{ mA}$	2.3 V	1.9			
E	B port		2.3 V	1.7			
		$I_{OH} = -6 \text{ mA}$	3 V	2.4			
		$I_{OH} = -8 \text{ mA}$	2.7 V	2			
		I _{OH} = -12 mA	3 V	2			
		I _{OL} = 100 μA	1.65 V to 3.6 V		0.2		
A port	I _{OL} = 4 mA	1.65 V		0.45			
	_	I _{OL} = 6 mA	2.3 V		0.4		
	A port		2.3 V		0.7	1	
		I _{OL} = 12 mA	2.7 V		0.4		
		I _{OL} = 24 mA	3 V		0.55	5	
V _{OL}		I _{OL} = 100 μA	1.65 V to 3.6 V		0.2	V	
		I _{OL} = 2 mA	1.65 V		0.45		
		I _{OL} = 4 mA	2.3 V		0.4		
E	B port		2.3 V		0.55		
		I _{OL} = 6 mA	3 V		0.55		
		I _{OL} = 8 mA	2.7 V		0.6		
		I _{OL} = 12 mA	3 V		0.8		
l _l		V _I = V _{CC} or GND	3.6 V		±5	μΑ	
		V _I = 0.58 V	4.05.1/	25			
		V _I = 1.07 V	1.65 V	-25			
		V _I = 0.7 V	0.01/	45			
I _{I(hold)}		V _I = 1.7 V	2.3 V	-45		μΑ	
(/		V _I = 0.8 V	21/	75			
		V _I = 2 V	3 V	- 75			
		$V_{I} = 0 \text{ to } 3.6 \text{ V}^{\ddagger}$	3.6 V		±500		
l _{OZ} §		$V_O = V_{CC}$ or GND	3.6 V		±10	μΑ	
ICC		$V_I = V_{CC}$ or GND, $I_O = 0$	3.6 V		40	μΑ	
ΔlCC		One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 3.6 V		750	μΑ	
	Control inputs	$V_I = V_{CC}$ or GND	3.3 V	3.5		pF	
	A or B ports	V _O = V _{CC} or GND	3.3 V	4.5		pF	

 $[\]mbox{\colored}$ For I/O ports, the parameter $\mbox{\colored}_{\mbox{OZ}}$ includes the input leakage current.



[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. ‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

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timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

		V _{CC} = 1.8 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock frequency		†		150		150		150	MHz
t _W	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high	†		3.3		3.3		3.3		ns
t _{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B, high or low	†		1.4		1.1		1.1		ns
th	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B, high or low	†	·	1.6	·	1.9		1.5	·	ns

[†] This information was not available at the time of publication.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} =	1.8 V	V _{CC} =	2.5 V 2 V	V _{CC} =	2.7 V	V _{CC} =	3.3 V 3 V	UNIT
	(INFO1)	(001F01)	MIN	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}			†		150		150		150		MHz
	А	В		†	1	5.9		5.8	1.2	4.9	
	В	А		†	1	5.7		5.1	1.2	4.3	
^t pd	LE SEL	А		†	1	5.6		5.2	1	4.4	ns
		В		†	1	6.1		5.9	1	5	
		А		†	1	6.9		6.6	1.1	5.6	
		А		†	1	6.7		6.4	1	5.4	
t _{en}	ŌĒ	В		†	1	7.2		7.1	1	6	ns
+		А		†	1	5.7		5	1.3	4.6	nc
^t dis	ŌĒ	В		†	1	6.2		5.5	1.3	5.1	ns

[†] This information was not available at the time of publication.

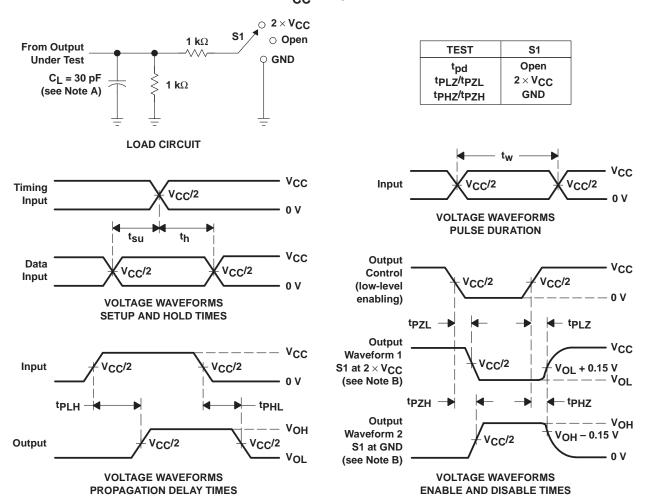
operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V V _{CC} = 2.5 V V _{CC} =		V _{CC} = 3.3 V	UNIT	
	PARAMETE	ir.	TEST CONDITIONS	TYP	TYP	TYP	UNIT
	Power dissipation	All outputs enabled	C ₁ = 50 pF. f = 10 MHz	Ť	37	41	pF
Cpd	C _{pd} capacitance	All outputs disabled	$C_L = 50 \text{ pF}, f = 10 \text{ MHz}$	†	4	7	рг

[†] This information was not available at the time of publication.

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PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.8 V



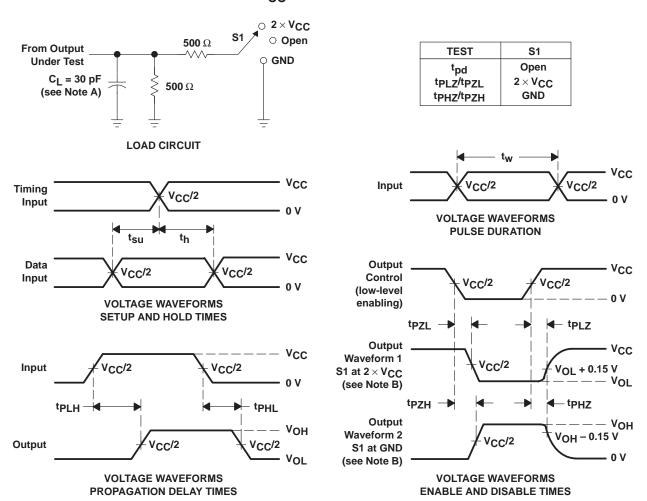
- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLZ and tpHZ are the same as t_{dis}.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 V \pm 0.2 V$



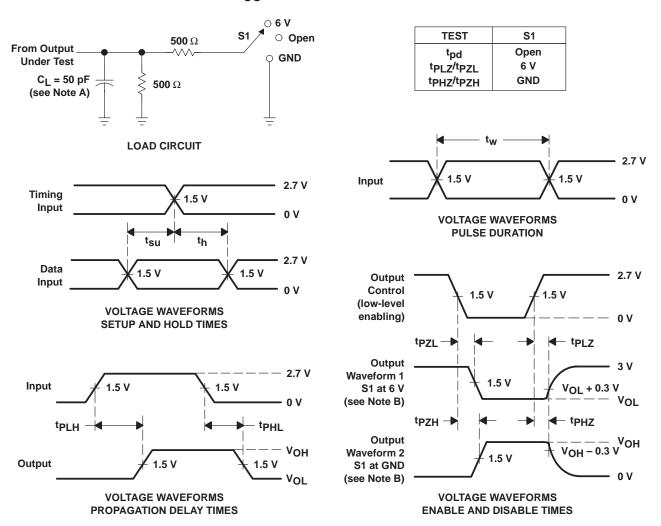
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

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PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.

 Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50~\Omega$, $t_\Gamma \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



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